100V N-CHANNEL ENHANCEMENT MODE MOSFET IN DPAK

SUMMARY

 $V_{(BR)DSS}$ =100 $V:R_{DS(on)}$ =0.085 Ω ; I_D =7.7A

DESCRIPTION

This new generation of Trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage power management applications.

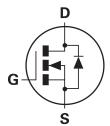


FEATURES DPAK

- Low on-resistance
- · Fast switching speed
- · Low gate drive
- D-Pak (T0-252) package

APPLICATIONS

- DC-DC Converters
- Power management functions
- Disconnect switches
- Motor control



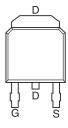
ORDERING INFORMATION

DEVICE	REEL	TAPE	QUANTITY PER
	SIZE	WIDTH	REEL
ZXMN10A09KTC	13"	16mm	2,500 units

DEVICE MARKING

 ZXMN 10A09K





TOP VIEW



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DSS}	100	V	
Gate-source voltage	V _{GS}	±20	V	
Continuous drain current @ V_{GS} =10V; T_A =25°C ^(b) @ V_{GS} =10V; T_A =70°C ^(b) @ V_{GS} =10V; T_A =25°C ^(a)	I _D	7.7 6.2 5	A A A	
Pulsed drain current ^(c)	I _{DM}	27	А	
Continuous source current (body diode) (b)	Is	11	А	
Pulsed source current (body diode) ^(c)	I _{SM}	27	А	
Power dissipation at T _A =25°C ^(a) Linear derating factor	P _D	4.3 34.4	W mW/°C	
Power dissipation at T _A =25°C ^(b) Linear derating factor	P _D	10.1 80.8	W mW/°C	
Power dissipation at T _A =25°C ^(d) Linear derating factor	P _D	2.15 17.2	W mW/°C	
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C	

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient ^(a)	$R_{\Theta JA}$	29	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	12.3	°C/W
Junction to ambient ^(d)	$R_{\Theta JA}$	58	°C/W

NOTES



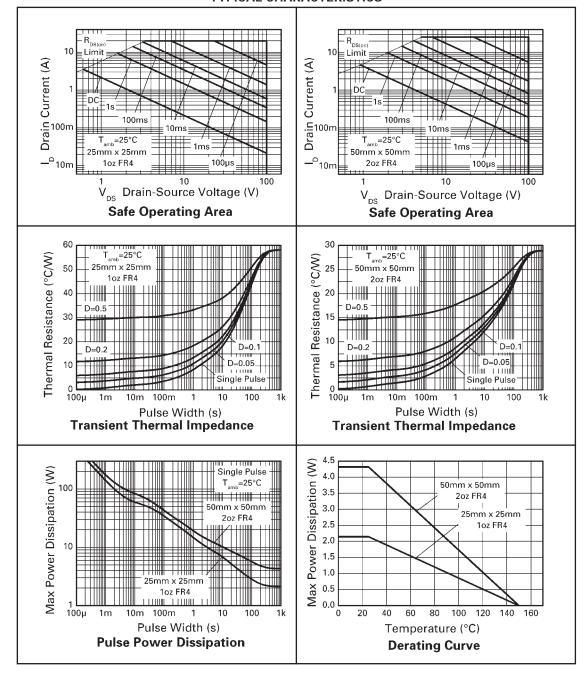
⁽a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

⁽b) For a device surface mounted on FR4 PCB measured at $t \le 10$ sec.

⁽c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D=0.02 pulse width=300 μs - pulse width limited by maximum junction temperature.

⁽d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

TYPICAL CHARACTERISTICS





ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated)

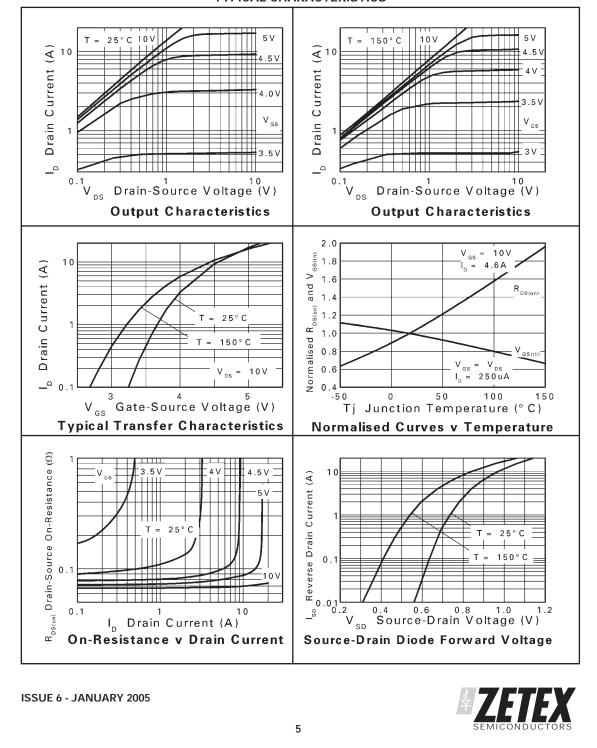
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS	
STATIC	ı						
Drain-source breakdown voltage	V _{(BR)DSS}	100			V	I _D = 250μA, V _{GS} =0V	
Zero gate voltage drain current	I _{DSS}			1	μΑ	V _{DS} = 100V, V _{GS} =0V	
Gate-body leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V	
Gate-source threshold voltage	V _{GS(th)}	2.0		4.0	V	$I_D=250\mu A$, $V_{DS}=V_{GS}$	
Static drain-source on-state resistance (1)	R _{DS(on)}			0.085	Ω	V _{GS} = 10V, I _D = 4.6A	
				0.100	Ω	V _{GS} = 6V, I _D = 4.2A	
Forward transconductance (1) (3)	9 _{fs}		10.7		S	V _{DS} = 15V, I _D = 4.6A	
DYNAMIC (3)				1			
Input capacitance	C _{iss}		1313		pF		
Output capacitance	C _{oss}		83		pF	$V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz	
Reverse transfer capacitance	C _{rss}		56		pF	1 = 11011712	
SWITCHING ^{(2) (3)}							
Turn-on-delay time	t _{d(on)}		6.8		ns		
Rise time	t _r		5.3		ns	V _{DD} = 50V, I _D = 1A	
Turn-off delay time	t _{d(off)}		27.5		ns	R _G ≅6.0Ω, V _{GS} = 10V	
Fall time	t _f		12.3		ns		
Total gate charge	Qg		17.2		nC	V _{DS} = 50V, V _{GS} = 6V I _D = 4.6A	
Total gate charge	Qg		26		nC		
Gate-source charge	Q _{gs}		5.6		nC	$V_{DS} = 50V, V_{GS} = 10V$ $I_{D} = 4.6A$	
Gate drain charge	Q _{gd}		7.6		nC	11D- 4.0V	
SOURCE-DRAIN DIODE	1	1	1	1	1	1	
Diode forward voltage ⁽¹⁾	V _{SD}		0.85	0.95	V	T _j =25°C, I _F = 4.7A, V _{GS} =0V	
Reverse recovery time ⁽³⁾	t _{rr}		40		ns	T _j =25°C, I _S = 3A,	
Reverse recovery charge (3)	Q _{rr}		62		nC	di/dt=100A/μs	

NOTES

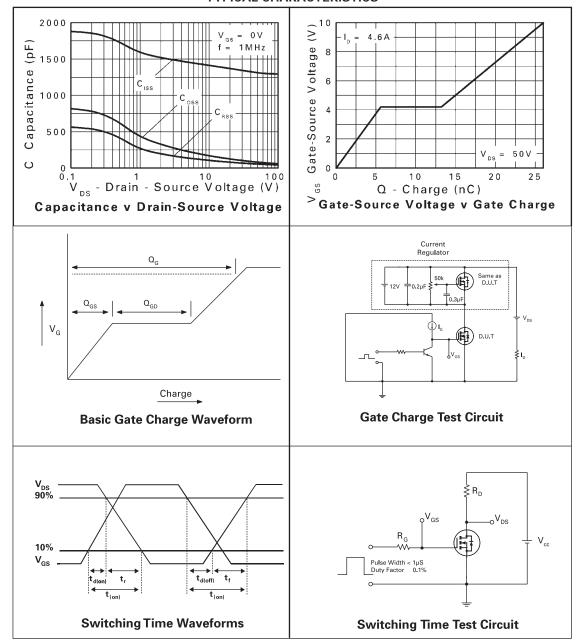
- (1) Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%.$
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.



TYPICAL CHARACTERISTICS

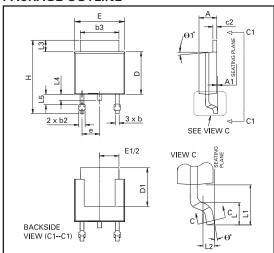


TYPICAL CHARACTERISTICS





PACKAGE OUTLINE



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millin	neters	Inc	hes	DIM	Millin	Millimeters		Inches	
DIIVI	Min	Max	Min	Max	DIIVI	Min	Max	Min	Max	
Α	2.18	2.38	0.086	0.094	е	2.30 BSC		0.090 BSC		
A1	_	0.127	_	0.005	Н	9.40	10.41	0.370	0.410	
b	0.635	0.89	0.025	0.035	L	1.40	1.78	0.055	0.070	
b2	0.762	1.114	0.030	0.045	L1	2.74 REF		0.108 REF		
b3	5.20	5.46	0.205	0.215	L2	0.051 BSC		0.020 BSC		
С	0.457	0.609	0.018	0.024	L3	0.89	1.27	0.035	0.050	
c2	0.457	0.584	0.018	0.023	L4	0.635	1.01	0.025	0.040	
D	5.97	6.22	0.235	0.245	L5	1.14	1.52	0.045	0.060	
D1	5.20	_	0.205	_	θ1°	0°	10°	0°	10°	
Е	6.35	6.73	0.250	0.265	θ°	0°	15°	0°	15°	
E1	4.32	_	0.170	_			_	_	_	

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